

Supplementary Materials: Oxygen Partial Pressure Impact on Characteristics of Indium Titanium Zinc Oxide Thin Film Transistor Fabricated via RF Sputtering

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This section includes: Figure S1, Table S1.

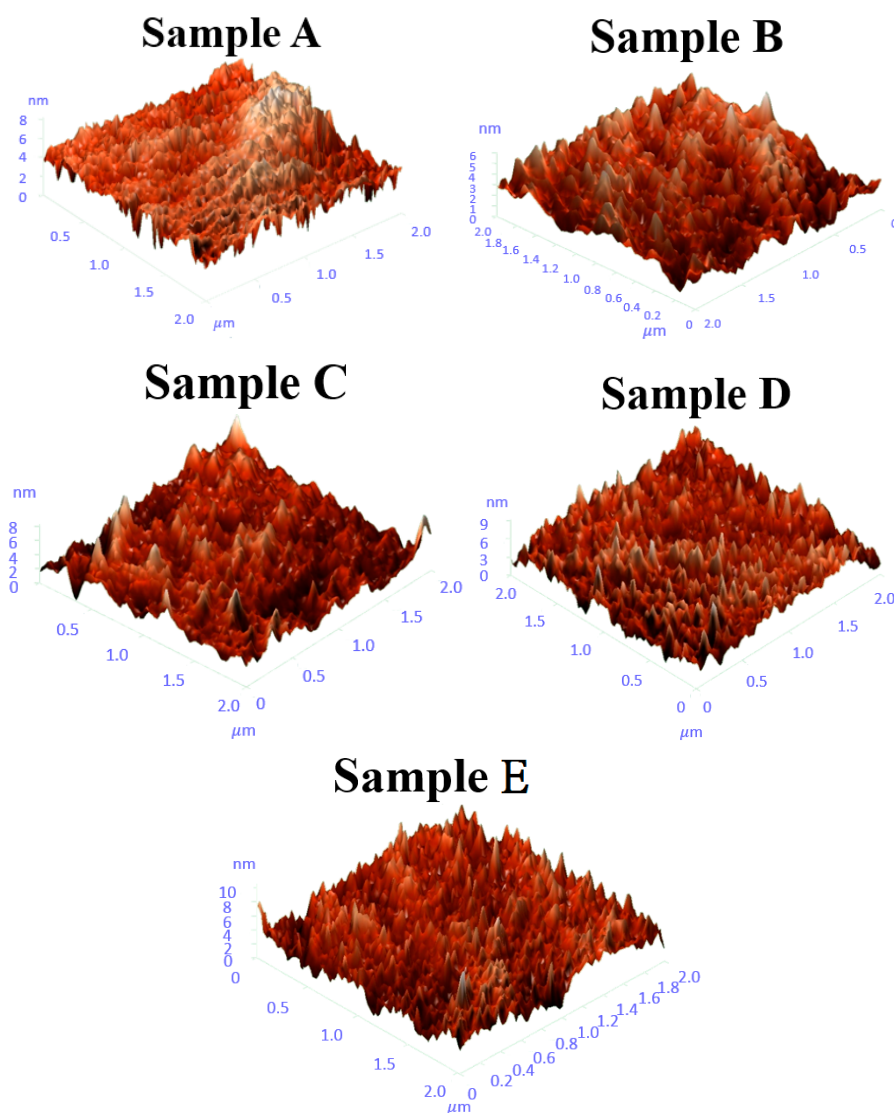


Figure S1. AFM images of each InTiZnO samples.

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Table S1. Electronic parameters for five Samples, with errors for Sample A, B, and C.

Samples	V_T (V)	μ_{eff} (cm ² /Vs)	On-off current ratio	SS (V/dec)	N_t (10 ¹¹ cm ⁻²)
Sample A (2%)	-0.35±0.1	1.625±0.001	1.5×10^5	0.320±0.003	4.6±0.1
Sample B (4%)	-0.9±0.01	0.884±0.003	5.5×10^5	0.410±0.002	6.2±0.1
Sample C (6%)	-0.5±0.03	0.235±0.001	1.1×10^3	1.62±0.04	28±1
Sample D (8%)	-1.4	0.006	1.4×10^2	2.46	43
Sample E (10%)	-4	0.004	1.1×10^1	8.57	150